

P3360/AEP 3630

①

Lecture 19

↳ refer to the printout on Transistor Amp. Config.

Darlington Pair

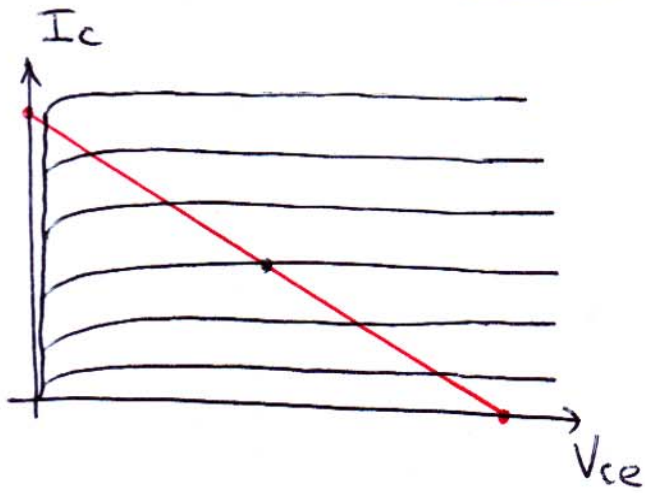
Note:

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Power in transistors



class A amplifiers

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-

pros :

cons :

class B

-

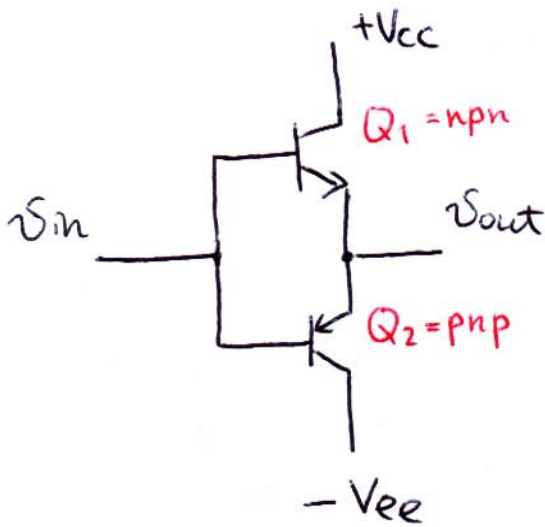
pros :

cons :

class C

-

Notes on push-pull complementary stage



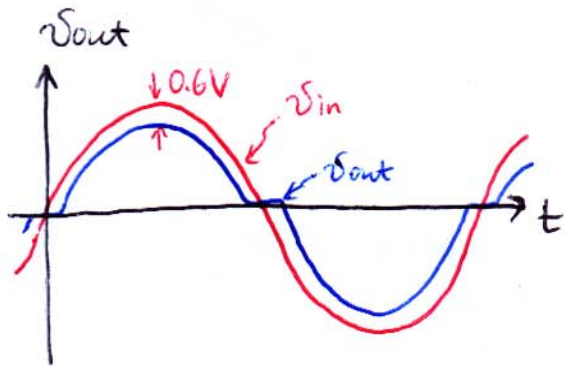
- "complementary" = both npn & pnp used

- "push-pull" only one transistor is ON (active), the other is OFF

- this is class B amplifier

- Note: both transistors cannot have forward biased be-junction simultaneously: $V_{be1} = V_{be2} = v_{in} - v_{out}$ b/c they are complementary

- $G \sim 1$ for volt. , can have $G \gg 1$ for current

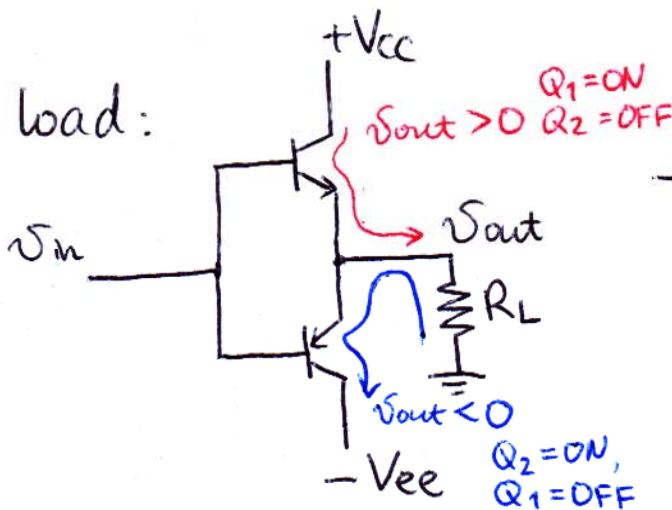


← Lab Manual, Fig 6.36

Note: there will be no cross-over distortions if no load is attached.

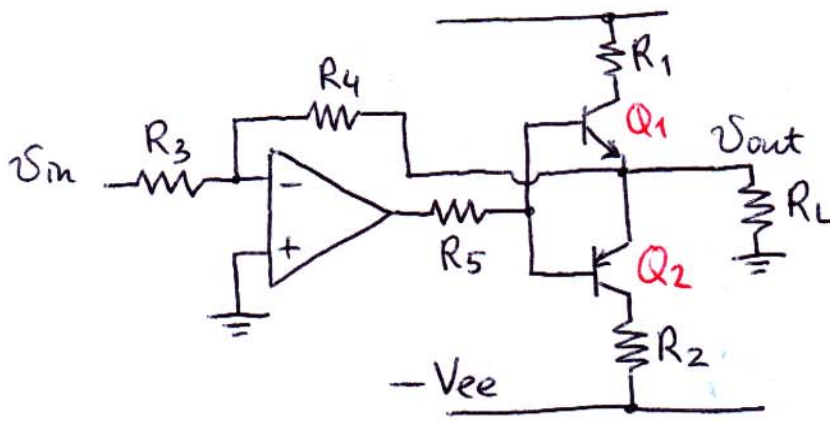
Q: why? A: no current can flow thru both $Q_{1,2}$, $\Rightarrow I_e \sim 0, V_{be} \sim 0$

With load:



- the current flows in the direction of emitter arrows for half the cycle, the other transistor is OFF

Push-pull amp with negative feedback to fix cross-over dist.

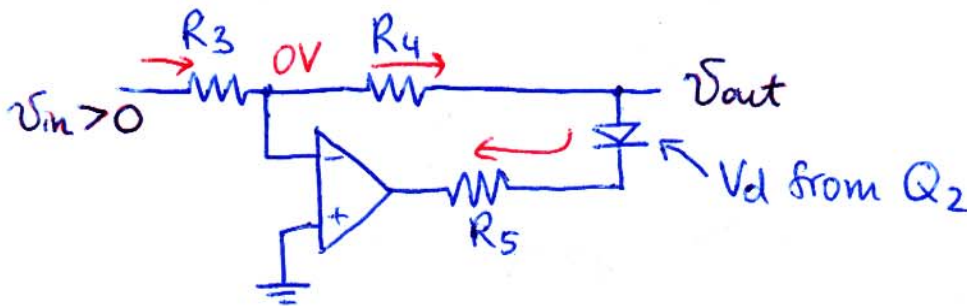


- basic idea : eliminate 0.6V diode drop using negative feedback

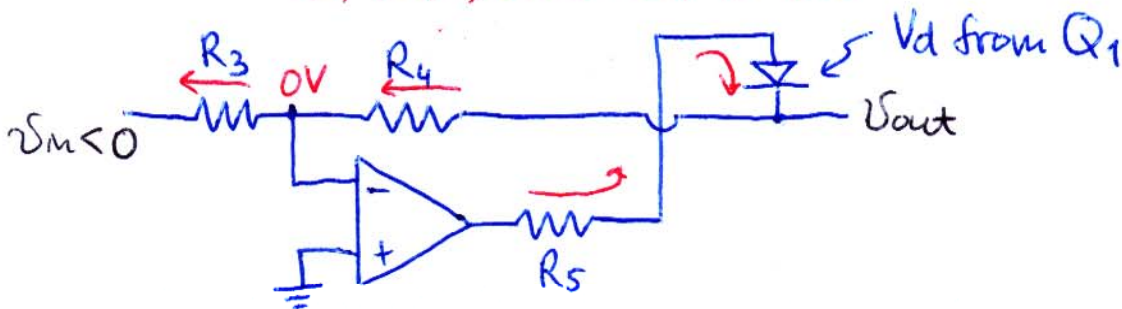
← Lab Manual, Fig 6.37
Exp. 6.10

Steps to understanding this circuit:

- 1) negative feedback keeps $V_- = V_+$
- 2) when $V_m > 0$, the current flows to the right across R_3, R_4 , and Q_2 is ON



- 3) when $V_m < 0$, the current flows to the left thru R_3, R_4 , and Q_1 is ON



In both cases
$$V_{out} = -R_4 \cdot I = -R_4 \frac{V_m}{R_3}$$

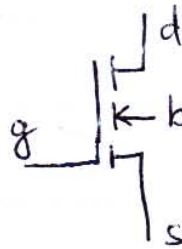
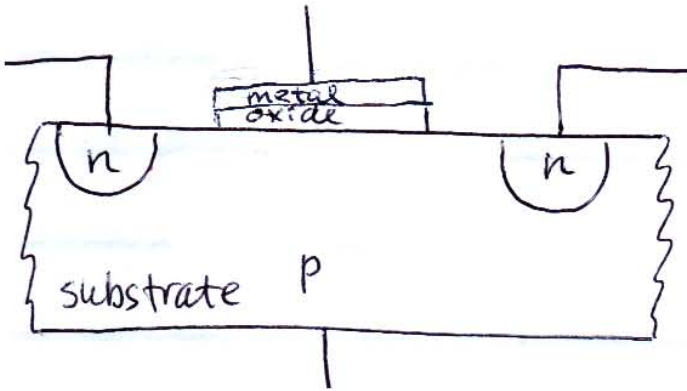
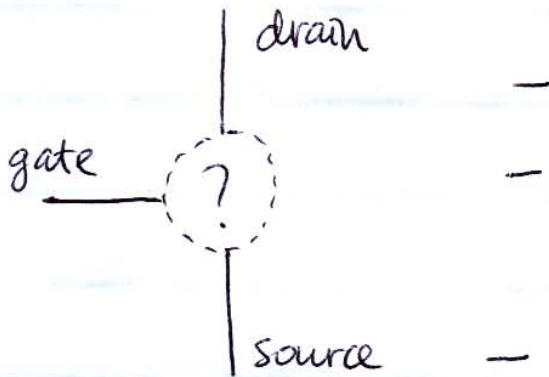
i.e. V_d does not come into the expression

Lecture 20

MOSFET

Metal-Oxide-Semiconductor Field _____ Transistor

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n-channel enhancement mode MOSFET



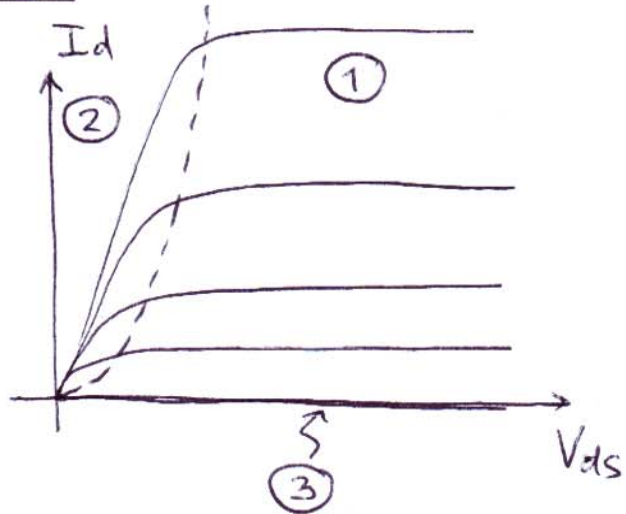
P-channel enhancement mode

(2)

to go between n-, p-channel types



Transfer characteristics



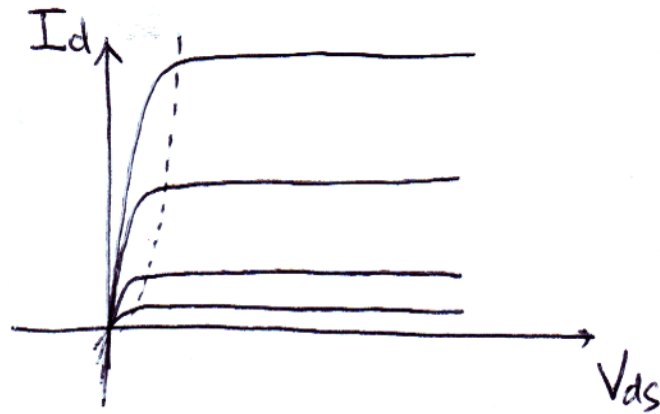
(1)

(2)

(3)

Lecture 21

MOSFET modes



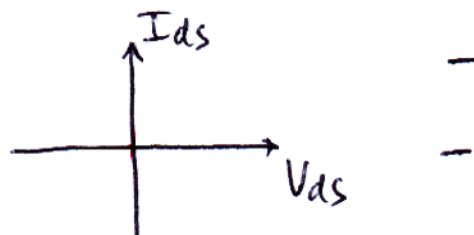
mathematical model

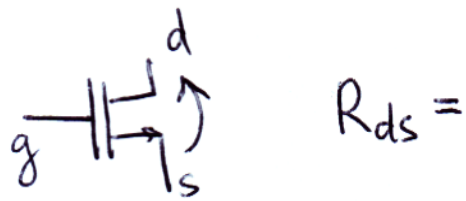
If $V_{gs} < V_T$,

Else if $V_{ds} < V_{gs} - V_T$,

else,

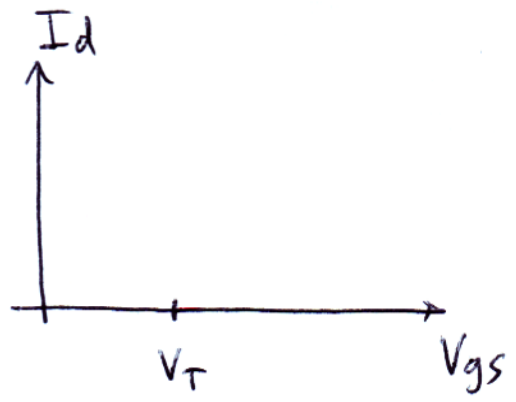
Ohmic region





$R_{ds} =$

saturation (= active) region



$I_d = K(V_{gs} - V_T)^2$

MOSFET circuit analysis

- ① large signal
- ② small-signal analysis

